

Keysight Technologies

Evaluation of Hot Carrier Induced Degradation of MOSFET Devices

Application Note

Keysight E5250A Low Leakage Switch Mainframe

Introduction

As device geometry scales down, reliability problems of semiconductor devices are increasing. The evaluation of hot carrier induced degradation becomes very important for developing reliable ULSI. This application note introduces you to Keysight Technologies, Inc. new solution for evaluation of hot carrier induced degradation of multiple MOSFET devices.

What is Hot Carrier Induced Degradation

Due to the short channel length of MOSFETs in today's ULSI, the electric field of the channel has become very high. The drain current easily ionizes electrons and holes around the drain (impact ionization), which cause hot electron and hot hole injection into the gate oxide (Drain Avalanche Hot Carrier; see Figure 1).

Some of the hot carriers are captured in the deep gate bias region, so the device's drain current (I_d), threshold voltage (V_{th}), and transconductance (G_m) are shifted.

Problems in Evaluation of Hot Carrier Induced Degradation

To efficiently evaluate hot carrier induced degradation of a MOSFET process, electrical stress should be applied to many devices for an extended period of time. Parameters such as I_d , V_{th} , and G_m must be repeatedly measured during this time. The resulting hot carrier life is estimated from the measured parameter shift versus stress time graph. (The test flow is shown in Figure 2.) Therefore, there are the following requirements in the test:

- Due to the long total test times required, devices should be tested in parallel to improve efficiency.
- Several stress conditions must be applied to the test devices to evaluate the relationship between parameter shifts and stress conditions.
- High resolution and precision measurements in current and voltage are required for evaluating sensitive parameter shifts.
- If the parameter measurements are not performed right after stress ends, the test results may be incorrect.

Until now, there has not been a switch that can meet these requirements and that does not sacrifice the measurement performance of the parameter analyzer.

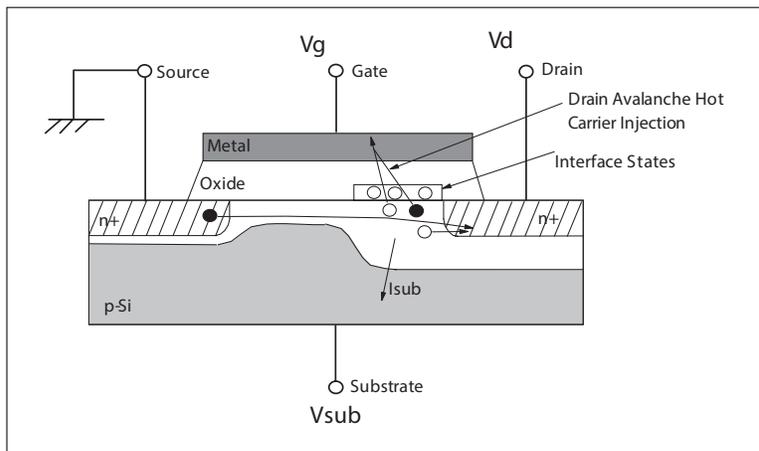


Figure 1. Drain avalanche hot carrier

New Solution using the Keysight E5250A

Combining the Keysight E5250A Option 501 24-channel multiplexer card and the Keysight 4155C/4156C parameter analyzer, you can configure a test system with up to 384 channels (using 4 Keysight E5250As including 4 multiplexer cards).

Each multiplexer card contains 3 individual 8-channel multiplexers as shown in Figure 3. Each block has a bias input port that you can connect to an external power supply for stressing multiple devices.

For accurate parameter measurements, the low leakage I-V input port is used to connect the Keysight 4155C/4156C to a device. This port has offset current of less than 100 fA. The example measurement result in Figure 4 shows that the subthreshold region of I_d - V_g curve can be stably measured.

If the power supply is disconnected from all the devices, there will be a lag time as SMUs are connected to each device and measured one by one. By using the single route mode and bias mode of the Keysight E5250A, a selected output channel of one multiplexer can be connected to an SMU while the other channels are connected to power supply output. With this capability, you can obtain correct test results by measuring parameters right after the stress termination.

How to Measure using the Keysight E5250A, 4155C/4156C, and Keysight 6626A

Figure 5 shows an example connection diagram for evaluation of hot carrier induced degradation using the Keysight E5250A, 4155C/4156C, and Keysight 6626A Multi-Channel Power Supply. In this example, one 24-channel multiplexer card is installed into a slot of the Keysight E5250A for test of 8 MOSFETs, which have common substrates.

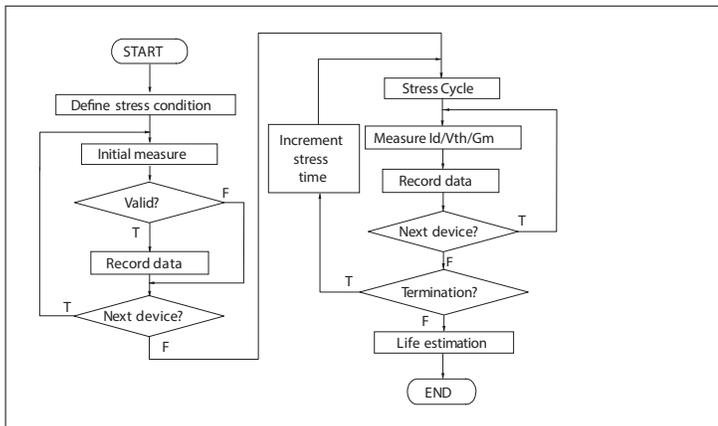


Figure 2. Flowchart of evaluating hot carrier induced degradation

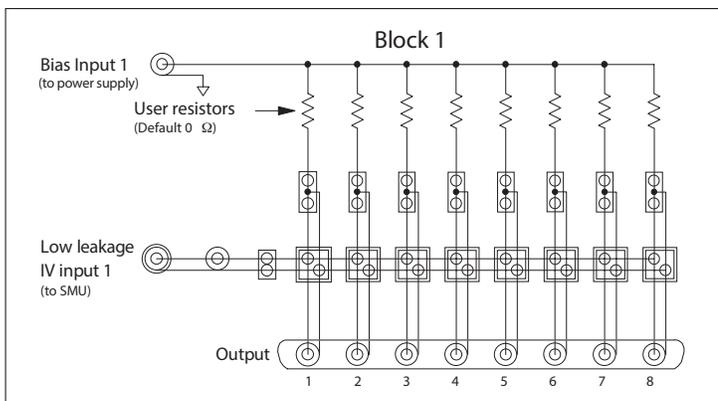


Figure 3. Block circuit diagram of multiplexer (one block).

Conclusion

Using the Keysight E5250A and 4155C/4156C with a power supply, you can electrically stress many devices in parallel. You can monitor each device one at a time while maintaining stress on the other devices, thus eliminating error due to measurement lag time. You can configure up to 384-channel system for hot carrier induced degradation evaluation of a large number of devices. By using individual bias input ports, you can perform test under various stress conditions. The multiplexer cards can be used for other long term reliability tests, such as TDDB and temperature lifetime.

Note: The information in this application note referring to the Keysight 4155C/4156C also applies to the Keysight 4155A/4156A and 4155B/4156B.

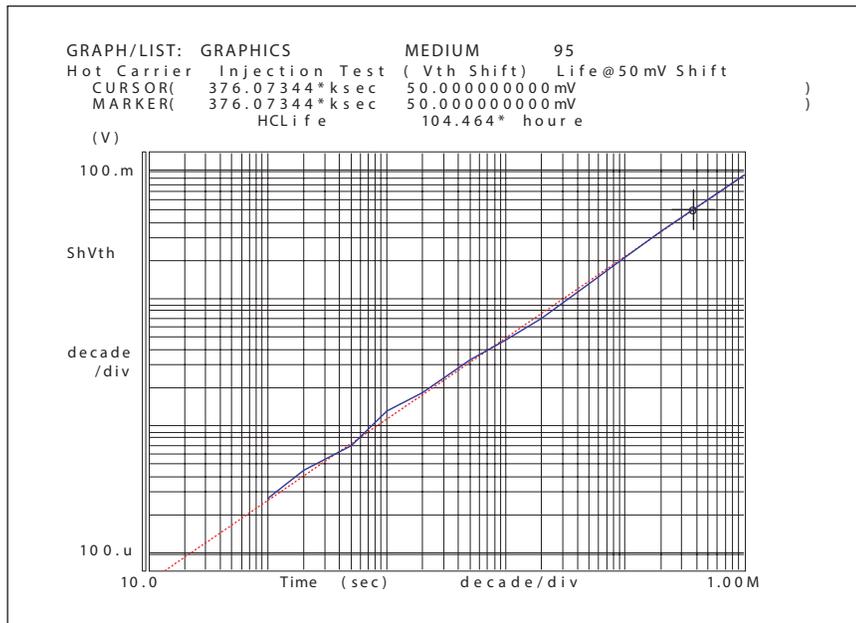
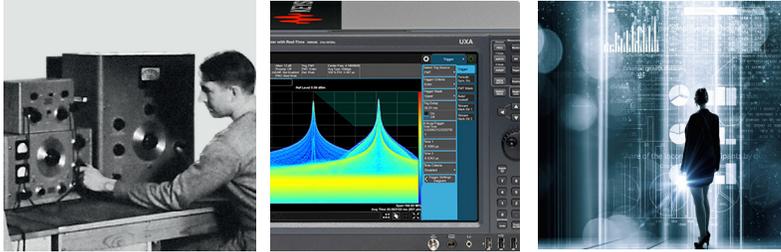


Figure 6. Estimation of hot carrier life

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